# **Voltage Regulator - CMOS**

# **Low Dropout** 300 mA

# **NCP114**

The NCP114 is 300 mA LDO that provides the engineer with a very stable, accurate voltage with low noise suitable for space constrained, noise sensitive applications. In order to optimize performance for battery operated portable applications, the NCP114 employs the dynamic quiescent current adjustment for very low Io consumption at no-load.

#### **Features**

- Operating Input Voltage Range: 1.7 V to 5.5 V
- Available in Fixed Voltage Options: 0.75 V to 3.6 V Contact Factory for Other Voltage Options
- Very Low Quiescent Current of Typ. 50 μA
- Standby Current Consumption: Typ. 0.1 μA
- Low Dropout: 135 mV Typical at 300 mA
- ±1% Accuracy at Room Temperature
- High Power Supply Ripple Rejection: 75 dB at 1 kHz
- Thermal Shutdown and Current Limit Protections
- Stable with a 1 µF Ceramic Output Capacitor
- Available in UDFN and TSOP Packages
- These are Pb-Free Devices

#### **Typical Applications**

- PDAs, Mobile phones, GPS, Smartphones
- Wireless Handsets, Wireless LAN, Bluetooth<sup>®</sup>, Zigbee<sup>®</sup>
- Portable Medical Equipment
- Other Battery Powered Applications

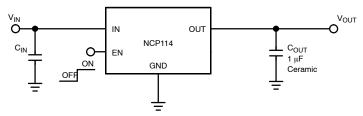


Figure 1. Typical Application Schematic



## ON Semiconductor®

www.onsemi.com

#### **MARKING DIAGRAMS**



UDFN4 **MX SUFFIX** CASE 517CU



XX = Specific Device Code

= Date Code



TSOP-5 SN SUFFIX **CASE 483** 

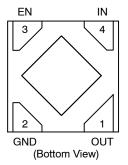


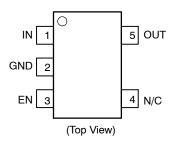
XXX = Specific Device Code = Assembly Location

= Year = Work Week

= Pb-Free Package (Note: Microdot may be in either location)

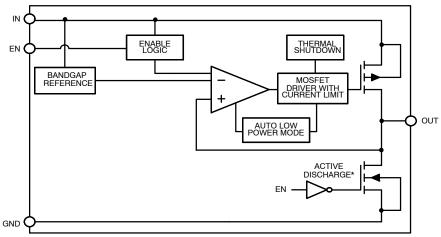
#### **PIN CONNECTIONS**





#### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 15 of this data sheet.



\*Active output discharge function is present only in NCP114AMXyyyTCG devices. yyy denotes the particular V<sub>OUT</sub> option.

Figure 2. Simplified Schematic Block Diagram

#### PIN FUNCTION DESCRIPTION

Pin No. (UDFN4)	Pin No. (TSOP5)	Pin Name	Description
1	5	OUT	Regulated output voltage pin. A small ceramic capacitor with minimum value of 1 $\mu F$ is needed from this pin to ground to assure stability.
2	2	GND	Power supply ground.
3	3	EN	Driving EN over 0.9 V turns on the regulator. Driving EN below 0.4 V puts the regulator into shutdown mode.
4	1	IN	Input pin. A small capacitor is needed from this pin to ground to assure stability.
-	4	N/C	Not connected. This pin can be tied to ground to improve thermal dissipation.
_	_	EPAD	Exposed pad should be connected directly to the GND pin. Soldered to a large ground copper plane allows for effective heat removal.

#### **ABSOLUTE MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V <sub>IN</sub>	-0.3 V to 6 V	V
Output Voltage	Vout	-0.3 V to VIN + 0.3 V or 6 V	V
Enable Input	VEN	-0.3 V to 6 V	V
Output Short Circuit Duration	tsc	∞	s
Maximum Junction Temperature	$T_{J(MAX)}$	150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C
ESD Capability, Human Body Model (Note 2)	ESD <sub>HBM</sub>	2000	٧
ESD Capability, Machine Model (Note 2)	ESD <sub>MM</sub>	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

- 2. This device series incorporates ESD protection and is tested by the following methods:
  - ESD Human Body Model tested per EIA/JESD22-A114,
  - ESD Machine Model tested per EIA/JESD22-A115,
  - Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

#### THERMAL CHARACTERISTICS (Note 3)

Rating	Symbol	Value	Unit
Thermal Characteristics, UDFN4 1x1 mm Thermal Resistance, Junction-to-Air	$R_{ heta JA}$	170	°C/W
Thermal Characteristics, TSOP-5 Thermal Resistance, Junction-to-Air	$R_{ heta JA}$	236	°C/W

3. Single component mounted on 1 oz, FR 4 PCB with 645 mm<sup>2</sup> Cu area.

#### **ELECTRICAL CHARACTERISTICS**

 $-40^{\circ}C \leq T_{J} \leq 85^{\circ}C; \ V_{IN} = V_{OUT(NOM)} + 1 \ V \ \text{for} \ V_{OUT} \ \text{options greater than 1.5 V. Otherwise} \ V_{IN} = 2.5 \ V, \ \text{whichever is greater;} \ I_{OUT} = 1 \ \text{mA}, \ C_{IN} = C_{OUT} = 1 \ \mu\text{F}, \ \text{unless otherwise noted.} \ V_{EN} = 0.9 \ V. \ \text{Typical values are at} \ T_{J} = +25^{\circ}C. \ \text{Min./Max. are for} \ T_{J} = -40^{\circ}C \ \text{and} \ T_{J} = +85^{\circ}C. \ \text{Min./max.} \ \text{True} \ \text{True$ respectively (Note 4).

Parameter	Test Conditio	Symbol	Min	Тур	Max	Unit	
Operating Input Voltage			V <sub>IN</sub>	1.7		5.5	V
		$V_{OUT} \le 2.0 \text{ V}$	V <sub>OUT</sub>	-40		+40	mV
Output Voltage Accuracy	$-40$ °C $\leq$ T <sub>J</sub> $\leq$ 85°C	V <sub>OUT</sub> > 2.0 V		-2		+2	%
Line Regulation	Vout + 0.5 V ≤ Vin ≤ 5.5 \	/ (V <sub>IN</sub> ≥ 1.7 V)	Reg <sub>LINE</sub>		0.01	0.1	%/V
Load Regulation – UDFN package	Java - 4 - 14 Ja 00	10 ··· 4	D		12	30	mV
Load Regulation - TSOP-5 package	IOUT = 1 mA to 30	00 mA	Reg <sub>LOAD</sub>		28	45	
Load Transient	$I_{OUT}$ = 1 mA to 300 mA or 3 in 1 $\mu$ s, $C_{OUT}$ =		Tran <sub>LOAD</sub>		-50/ +30		mV
		V <sub>OUT</sub> = 1.5 V			365	460	
		V <sub>OUT</sub> = 1.85 V			245	330	
		V <sub>OUT</sub> = 2.8 V	.,		155	230	.,
Dropout Voltage – UDFN package (Note 5)	I <sub>OUT</sub> = 300 mA	V <sub>OUT</sub> = 3.0 V	$V_{DO}$		145	220	mV
		V <sub>OUT</sub> = 3.1 V			140	210	
		V <sub>OUT</sub> = 3.3 V			135	200	
		V <sub>OUT</sub> = 1.5 V			380	485	- mV
		V <sub>OUT</sub> = 1.85 V	V <sub>DO</sub>		260	355	
D TOOD (N 5)	I <sub>OUT</sub> = 300 mA	V <sub>OUT</sub> = 2.8 V			170	255	
Dropout Voltage – TSOP package (Note 5)		V <sub>OUT</sub> = 3.0 V			160	245	
		V <sub>OUT</sub> = 3.1 V			155	235	
		V <sub>OUT</sub> = 3.3 V			150	225	
Output Current Limit	V <sub>OUT</sub> = 90% V <sub>OU</sub>	T(nom)	I <sub>CL</sub>	300	600		mA
Ground Current	Iout = 0 mA		ΙQ		50	95	μΑ
Shutdown Current	VEN ≤ 0.4 V, VIN =	5.5 V	I <sub>DIS</sub>		0.01	1	μΑ
EN Pin Threshold Voltage High Threshold Low Threshold	V <sub>EN</sub> Voltage incre V <sub>EN</sub> Voltage decre	easing easing	V <sub>EN_HI</sub> V <sub>EN_LO</sub>	0.9		0.4	٧
EN Pin Input Current	VEN = 5.5 V		I <sub>EN</sub>		0.3	1.0	μА
Power Supply Rejection Ratio	V <sub>IN</sub> = 3.6 V, V <sub>OUT</sub> = 3.1 V I <sub>OUT</sub> = 150 mA	f = 1 kHz	PSRR		75		dB
Output Noise Voltage	V <sub>IN</sub> = 2.5 V, V <sub>OUT</sub> = 1.8 V, I <sub>OUT</sub> = 150 mA f = 10 Hz to 100 kHz		V <sub>N</sub>		70		$\mu V_{rms}$
Thermal Shutdown Temperature	Temperature increasing from T <sub>J</sub> = +25°C		T <sub>SD</sub>		160		°C
Thermal Shutdown Hysteresis	Temperature falling f	rom T <sub>SD</sub>	T <sub>SDH</sub>		20		°C
Active Output Discharge Resistance	VEN < 0.4 V, Version	n A only	R <sub>DIS</sub>		100		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T<sub>J</sub> = T<sub>A</sub> = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

5. Characterized when Vout falls 100 mV below the regulated voltage at Vin = Vout(NOM) + 1 V.

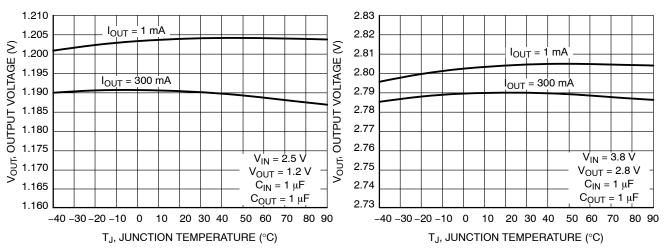


Figure 3. Output Voltage vs. Temperature V<sub>OUT</sub> = 1.2 V (UDFN)

Figure 4. Output Voltage vs. Temperature V<sub>OUT</sub> = 2.8 V (UDFN)

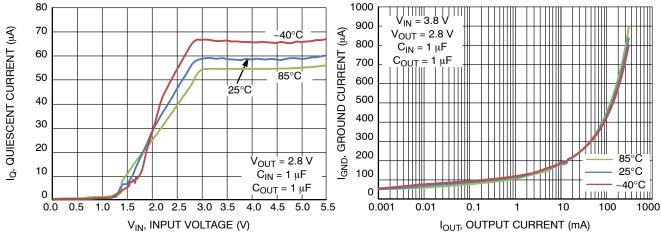


Figure 5. Quiescent Current vs. Input Voltage

Figure 6. Ground Current vs. Output Current

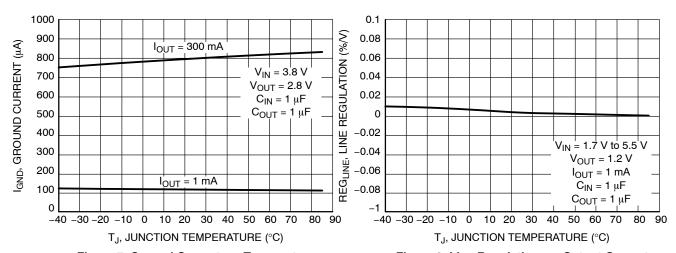


Figure 7. Ground Current vs. Temperature

Figure 8. Line Regulation vs. Output Current  $V_{OUT} = 1.2 \text{ V}$ 

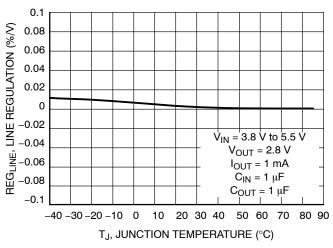


Figure 9. Line Regulation vs. Temperature  $V_{OUT} = 2.8 \text{ V}$ 

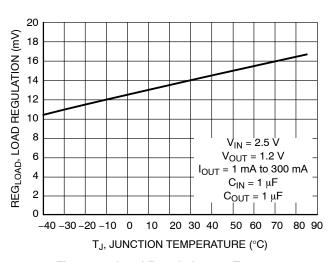


Figure 10. Load Regulation vs. Temperature  $V_{OUT} = 1.2 \text{ V (UDFN)}$ 

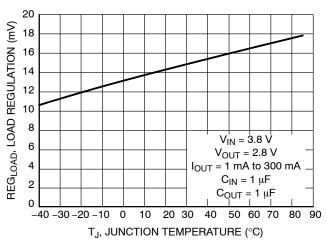


Figure 11. Load Regulation vs. Temperature V<sub>OUT</sub> = 2.8 V (UDFN)

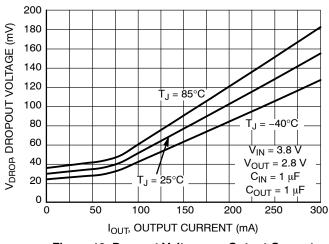


Figure 12. Dropout Voltage vs. Output Current V<sub>OUT</sub> = 2.8 V (UDFN)

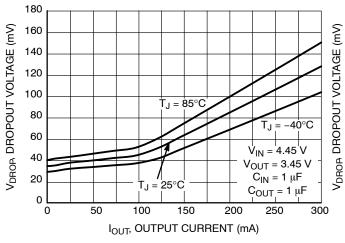


Figure 13. Dropout Voltage vs. Output Current V<sub>OUT</sub> = 3.45 V (UDFN)

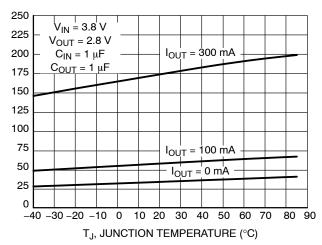
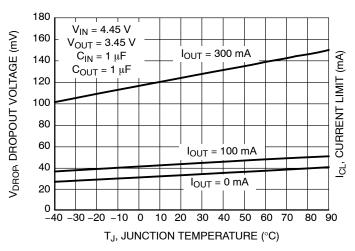


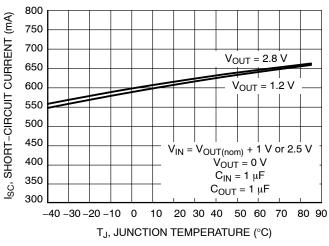
Figure 14. Dropout Voltage vs. Temperature V<sub>OUT</sub> = 2.8 V (UDFN)



800 750 700 650  $V_{OUT} = \overline{2.8 \text{ V}}$ 600 V<sub>OUT</sub> = 1.2 V 550 500 450  $V_{IN} = V_{OUT(nom)} + 1 \text{ V or } 2.5 \text{ V}$   $V_{OUT} = 90\% V_{OUT(nom)}$ 400  $C_{IN} = 1 \mu F$ 350  $C_{OUT} = 1 \mu F$ 300 10 20 30 40 50 60 70 80 90 -40 -30 -20 -10 0 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 15. Dropout Voltage vs. Temperature V<sub>OUT</sub> = 3.45 V (UDFN)

Figure 16. Current Limit vs. Temperature



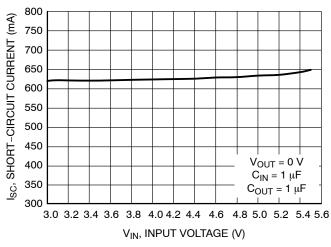
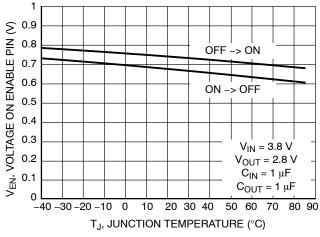


Figure 17. Short-Circuit Current vs. Temperature

Figure 18. Short-Circuit Current vs. Input Voltage



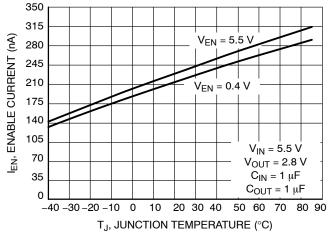


Figure 19. Enable Voltage Threshold vs. Temperature

Figure 20. Current to Enable Pin vs. Temperature

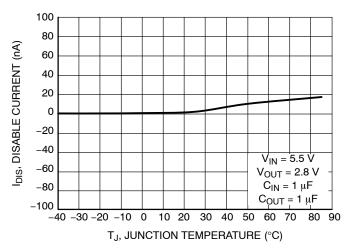
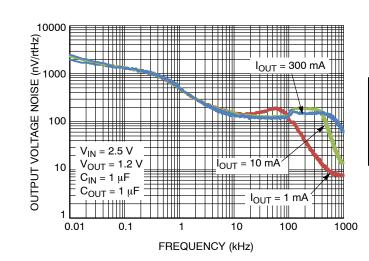
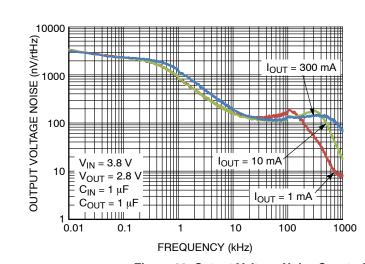


Figure 21. Disable Current vs. Temperature



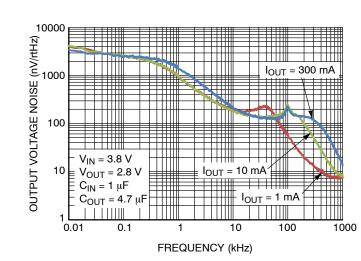
,	RMS Output Noise (μV)			
lоит	10 Hz – 100 kHz	100 Hz – 100 kHz		
1 mA	60.93	59.11		
10 mA	52.73	50.63		
300 mA	52.06	50.17		

Figure 22. Output Voltage Noise Spectral Density for  $V_{OUT}$  = 1.2 V,  $C_{OUT}$  = 1  $\mu F$ 



RMS Output Noise (μV)			
10 Hz – 100 kHz	100 Hz – 100 kHz		
79.23	74.66		
75.03	70.37		
87.74	83.79		
	10 Hz – 100 kHz 79.23 75.03		

Figure 23. Output Voltage Noise Spectral Density for  $V_{OUT}$  = 2.8 V,  $C_{OUT}$  = 1  $\mu F$ 



	RMS Output Noise (μV)			
I <sub>OUT</sub>	10 Hz – 100 kHz	100 Hz – 100 kHz		
1 mA	80.17	75.29		
10 mA	81.28	76.46		
300 mA	93.23	89.62		

Figure 24. Output Voltage Noise Spectral Density for  $V_{OUT}$  = 2.8 V,  $C_{OUT}$  = 4.7  $\mu F$ 

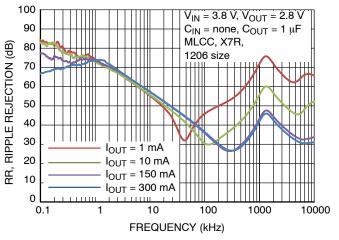


Figure 25. Power Supply Rejection Ratio,  $V_{OUT}$  = 2.8 V,  $C_{OUT}$  = 1  $\mu F$ 

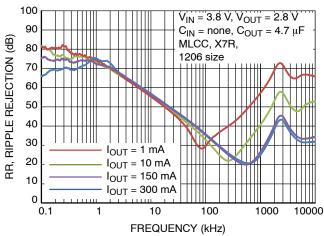


Figure 26. Power Supply Rejection Ratio,  $V_{OUT}$  = 2.8 V,  $C_{OUT}$  = 4.7  $\mu F$ 

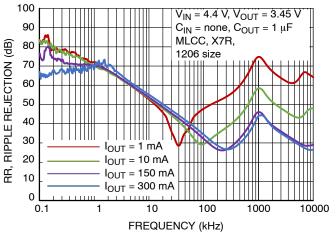


Figure 27. Power Supply Rejection Ratio,  $V_{OUT}$  = 3.45 V,  $C_{OUT}$  = 1  $\mu F$ 

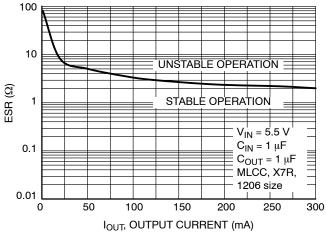


Figure 28. Output Capacitor ESR vs. Output Current

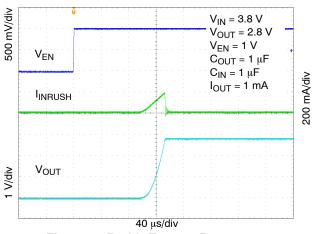


Figure 29. Enable Turn-on Response,  $C_{OUT}$  = 1  $\mu F$ ,  $I_{OUT}$  = 1 mA

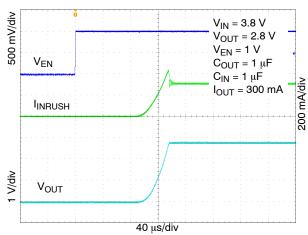


Figure 30. Enable Turn-on Response,  $C_{OUT} = 1 \mu F$ ,  $I_{OUT} = 300 \text{ mA}$ 

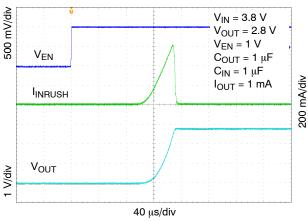


Figure 31. Enable Turn-on Response,  $C_{OUT} = 4.7 \mu F, I_{OUT} = 1 mA$ 

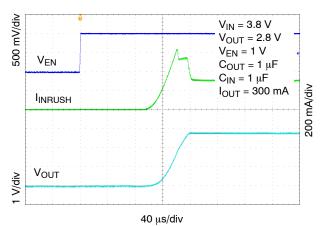


Figure 32. Enable Turn-on Response,  $C_{OUT} = 4.7~\mu F, \, I_{OUT} = 300~mA$ 

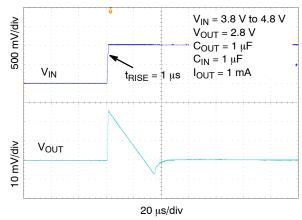


Figure 33. Line Transient Response – Rising Edge,  $V_{OUT}$  = 2.8 V,  $I_{OUT}$  = 1 mA

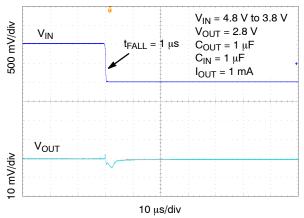


Figure 34. Line Transient Response – Falling Edge,  $V_{OUT}$  = 2.8 V,  $I_{OUT}$  = 1 mA

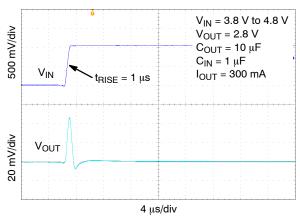


Figure 35. Line Transient Response – Rising Edge, V<sub>OUT</sub> = 2.8 V, I<sub>OUT</sub> = 300 mA

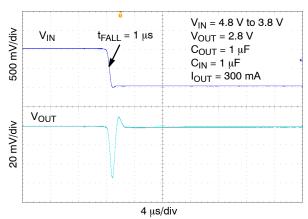


Figure 36. Line Transient Response – Falling Edge, V<sub>OUT</sub> = 2.8 V, I<sub>OUT</sub> = 300 mA

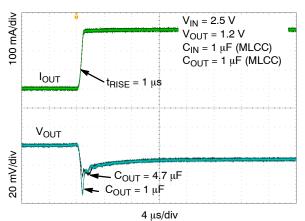


Figure 37. Load Transient Response – Rising Edge,  $V_{OUT}$  = 1.2 V,  $I_{OUT}$  = 1 mA to 300 mA,  $C_{OUT}$  = 1  $\mu$ F, 4.7  $\mu$ F

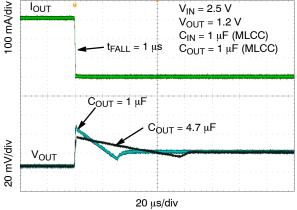


Figure 38. Load Transient Response – Falling Edge,  $V_{OUT}$  = 1.2 V,  $I_{OUT}$  = 1 mA to 300 mA,  $C_{OUT}$  = 1  $\mu$ F, 4.7  $\mu$ F

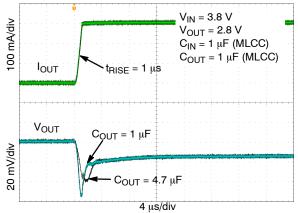


Figure 39. Load Transient Response – Rising Edge,  $V_{OUT}$  = 2.8 V,  $I_{OUT}$  = 1 mA to 300 mA,  $C_{OUT}$  = 1  $\mu$ F, 4.7  $\mu$ F

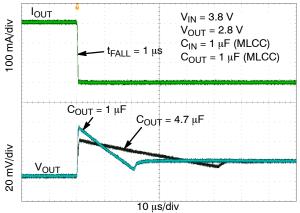


Figure 40. Load Transient Response – Falling Edge,  $V_{OUT}$  = 2.8 V,  $I_{OUT}$  = 1 mA to 300 mA,  $C_{OUT}$  = 1  $\mu$ F, 4.7  $\mu$ F

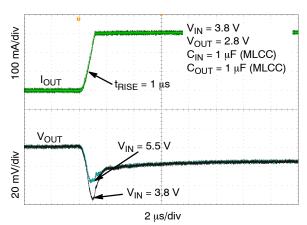


Figure 41. Load Transient Response – Rising Edge,  $V_{OUT}$  = 2.8 V,  $I_{OUT}$  = 1 mA to 300 mA,  $V_{IN}$  = 3.8 V, 5.5 V

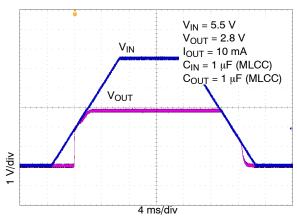


Figure 43. Turn-on/off - Slow Rising V<sub>IN</sub>

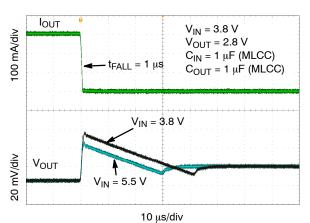


Figure 42. Load Transient Response – Falling Edge,  $V_{OUT}$  = 2.8 V,  $I_{OUT}$  = 1 mA to 300 mA,  $V_{IN}$  = 3.8 V, 5.5 V

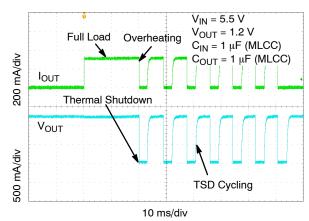


Figure 44. Short-Circuit and Thermal Shutdown

#### **APPLICATIONS INFORMATION**

#### General

The NCP114 is a high performance 300 mA Low Dropout Linear Regulator. This device delivers very high PSRR (over 75 dB at 1 kHz) and excellent dynamic performance as load/line transients. In connection with very low quiescent current this device is very suitable for various battery powered applications such as tablets, cellular phones, wireless and many others. The device is fully protected in case of output overload, output short circuit condition and overheating, assuring a very robust design.

#### Input Capacitor Selection (CIN)

It is recommended to connect at least a 1  $\mu$ F Ceramic X5R or X7R capacitor as close as possible to the IN pin of the device. This capacitor will provide a low impedance path for unwanted AC signals or noise modulated onto constant input voltage. There is no requirement for the min. /max. ESR of the input capacitor but it is recommended to use ceramic capacitors for their low ESR and ESL. A good input capacitor will limit the influence of input trace inductance and source resistance during sudden load current changes. Larger input capacitor may be necessary if fast and large load transients are encountered in the application.

## Output Decoupling (COUT)

The NCP114 requires an output capacitor connected as close as possible to the output pin of the regulator. The recommended capacitor value is 1  $\mu F$  and X7R or X5R dielectric due to its low capacitance variations over the specified temperature range. The NCP114 is designed to remain stable with minimum effective capacitance of 0.22 $\mu F$  to account for changes with temperature, DC bias and package size. Especially for small package size capacitors such as 0402 the effective capacitance drops rapidly with the applied DC bias.

There is no requirement for the minimum value of Equivalent Series Resistance (ESR) for the  $C_{OUT}$  but the maximum value of ESR should be less than 2  $\Omega$ . Larger output capacitors and lower ESR could improve the load transient response or high frequency PSRR. It is not recommended to use tantalum capacitors on the output due to their large ESR. The equivalent series resistance of tantalum capacitors is also strongly dependent on the temperature, increasing at low temperature.

#### **Enable Operation**

The NCP114 uses the EN pin to enable/disable its device and to deactivate/activate the active discharge function.

If the EN pin voltage is <0.4 V the device is guaranteed to be disabled. The pass transistor is turned—off so that there is virtually no current flow between the IN and OUT. The active discharge transistor is active so that the output voltage  $V_{OUT}$  is pulled to GND through a 100  $\Omega$  resistor. In the

disable state the device consumes as low as typ. 10 nA from the  $V_{\text{IN}}$ .

If the EN pin voltage >0.9 V the device is guaranteed to be enabled. The NCP114 regulates the output voltage and the active discharge transistor is turned–off.

The EN pin has internal pull-down current source with typ. value of 300 nA which assures that the device is turned-off when the EN pin is not connected. In the case where the EN function isn't required the EN should be tied directly to IN.

#### **Output Current Limit**

Output Current is internally limited within the IC to a typical 600 mA. The NCP114 will source this amount of current measured with a voltage drops on the 90% of the nominal  $V_{OUT}$ . If the Output Voltage is directly shorted to ground ( $V_{OUT}$  = 0 V), the short circuit protection will limit the output current to 630 mA (typ). The current limit and short circuit protection will work properly over whole temperature range and also input voltage range. There is no limitation for the short circuit duration.

#### **Thermal Shutdown**

When the die temperature exceeds the Thermal Shutdown threshold ( $T_{SD}$  –  $160^{\circ}$ C typical), Thermal Shutdown event is detected and the device is disabled. The IC will remain in this state until the die temperature decreases below the Thermal Shutdown Reset threshold ( $T_{SDU}$  –  $140^{\circ}$ C typical). Once the IC temperature falls below the  $140^{\circ}$ C the LDO is enabled again. The thermal shutdown feature provides the protection from a catastrophic device failure due to accidental overheating. This protection is not intended to be used as a substitute for proper heat sinking.

#### **Power Dissipation**

As power dissipated in the NCP114 increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part.

The maximum power dissipation the NCP114 can handle is given by:

$$P_{D(MAX)} = \frac{\left[85^{\circ}C - T_{A}\right]}{\theta_{JA}} \tag{eq. 1}$$

The power dissipated by the NCP114 for given application conditions can be calculated from the following equations:

$$P_{D} \approx V_{IN} \! \! \left( I_{GND} @ I_{OUT} \right) + I_{OUT} \! \! \left( V_{IN} - V_{OUT} \right) \hspace{0.5cm} \text{(eq. 2)}$$

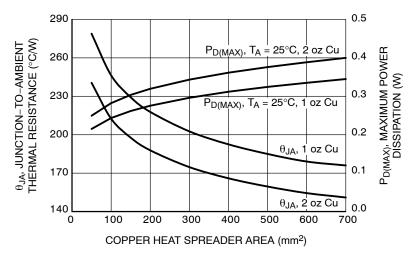


Figure 45. θ<sub>JA</sub> vs. Copper Area (uDFN4)

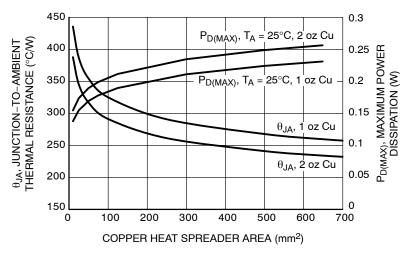


Figure 46.  $\theta_{JA}$  vs. Copper Area (TSOP-5)

#### **Reverse Current**

The PMOS pass transistor has an inherent body diode which will be forward biased in the case that  $V_{OUT} > V_{IN}$ . Due to this fact in cases, where the extended reverse current condition can be anticipated the device may require additional external protection.

## **Power Supply Rejection Ratio**

The NCP114 features very good Power Supply Rejection ratio. If desired the PSRR at higher frequencies in the range  $100~\rm kHz-10~MHz$  can be tuned by the selection of  $C_{OUT}$  capacitor and proper PCB layout.

#### Turn-On Time

The turn–on time is defined as the time period from EN assertion to the point in which  $V_{OUT}$  will reach 98% of its

nominal value. This time is dependent on various application conditions such as  $V_{OUT(NOM)}$ ,  $C_{OUT}$  and  $T_A$ . For example typical value for  $V_{OUT}$  = 1.2 V,  $C_{OUT}$  = 1  $\mu$ F,  $I_{OUT}$  = 1 mA and  $T_A$  = 25°C is 90  $\mu$ s.

## **PCB Layout Recommendations**

To obtain good transient performance and good regulation characteristics place  $C_{\rm IN}$  and  $C_{\rm OUT}$  capacitors close to the device pins and make the PCB traces wide. In order to minimize the solution size, use 0402 capacitors. Larger copper area connected to the pins will also improve the device thermal resistance. The actual power dissipation can be calculated from the equation above (Equation 2). Expose pad should be tied the shortest path to the GND pin.

## ORDERING INFORMATION

Device	Voltage Option	Marking	Marking Rotation	Option	Package	Shipping <sup>†</sup>
NCP114AMX075TCG	0.75 V	AW	0°			
NCP114AMX080TCG	0.80 V	AT	0°			
NCP114AMX090TAG	0.9 V	AP	0°			
NCP114AMX090TCG	0.9 V	AP	0°			
NCP114AMX092TAG	0.92 V	A2	0°			
NCP114AMX100TCG	1.0 V	6	180°			
NCP114AMX105TCG	1.05 V	R	0°			
NCP114AMX110TBG	1.1 V	F	180°			
NCP114AMX110TCG	1.1 V	F	180°			
NCP114AMX115TCG	1.15 V	AM	0°			
NCP114AMX120TBG	1.2 V	Т	0°			
NCP114AMX120TCG	1.2 V	Т	0°			
NCP114AMX125TCG	1.25 V	А	180°			
NCP114AMX130TCG	1.3 V	AA	0°			
NCP114AMX135TCG	1.35 V	AN	0°			
NCP114AMX150TCG	1.5 V	V	0°			
NCP114AMX160TCG	1.6 V	2	180°			
NCP114AMX180TBG	1.8 V	J	180°			
NCP114AMX180TCG	1.8 V	J	180°			
NCP114AMX185TCG	1.85 V	Y	0°	With active output	UDFN4	0000 / Tana 8 Daal
NCP114AMX210TCG	2.1 V	L	180°	discharge function	(Pb-Free)	3000 / Tape & Reel
NCP114AMX220TCG	2.2 V	Q	180°			
NCP114AMX240TCG	2.4 V	AH	0°			
NCP114AMX250TBG	2.5 V	AF	0°			
NCP114AMX250TCG	2.5 V	AF	0°			
NCP114AMX260TCG	2.6 V	Т	180°			
NCP114AMX270TCG	2.7 V	AJ	0°			
NCP114AMX280TBG	2.8 V	2	0°			
NCP114AMX280TCG	2.8 V	2	0°			
NCP114AMX285TCG	2.85 V	3	0°			
NCP114AMX290TCG	2.9 V	AZ	0°			
NCP114AMX300TCG	3.0 V	4	0°			
NCP114AMX310TBG	3.1 V	5	0°			
NCP114AMX310TCG	3.1 V	5	0°			
NCP114AMX320TCG	3.2 V	AG	0°			
NCP114AMX330TBG	3.3 V	6	0°			
NCP114AMX330TCG	3.3 V	6	0°			
NCP114AMX345TCG	3.45 V	AC	0°			
NCP114AMX350TCG	3.5 V	4	180°			
NCP114AMX360TCG	3.6 V	AU	0°		1	

#### **ORDERING INFORMATION**

Device	Voltage Option	Marking	Marking Rotation	Option	Package	Shipping <sup>†</sup>
NCP114BMX075TCG	0.75 V	CW	0°			
NCP114BMX100TCG	1.0 V	6	270°			
NCP114BMX120TCG	1.2 V	Т	90°			
NCP114BMX150TCG	1.5 V	V	90°			
NCP114BMX180TCG	1.8 V	J	270°	Without active output discharge function	UDFN4 (Pb-Free)	3000 / Tape & Reel
NCP114BMX250TCG	2.5 V	CF	0°	g	(* 2 * * * * * * * * * * * * * * * * * *	
NCP114BMX280TCG	2.8 V	2	90°			
NCP114BMX300TCG	3.0 V	4	90°			
NCP114BMX330TCG	3.3 V	6	90°			

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ORDERING INFORMATION**

Device	Voltage Option	Marking	Option	Package	Shipping <sup>†</sup>	
NCP114ASN080T1G	0.8 V	CAY				
NCP114ASN120T1G	1.2 V	CAC				
NCP114ASN120T2G						
NCP114ASN150T1G	1.5 V	CAX				
NCP114ASN150T2G	1					
NCP114ASN180T1G	1.8 V	CAD				
NCP114ASN180T2G						
NCP114ASN250T1G	2.5 V	CAG				
NCP114ASN250T2G			With output active discharge function	T00D 5		
NCP114ASN260T1G	2.6 V	CAQ		TSOP-5 (Pb-Free)	3000 / Tape & Reel	
NCP114ASN270T1G	2.7 V	CAV				
NCP114ASN280T1G	2.8 V	CAH				
NCP114ASN280T2G						
NCP114ASN290T1G	2.9 V	CAU				
NCP114ASN300T1G	3.0 V	CAK				
NCP114ASN330T1G	3.3 V	CAL				
NCP114ASN330T2G	1					
NCP114BSN330T1G	3.3 V	CDL	Without output active discharge			

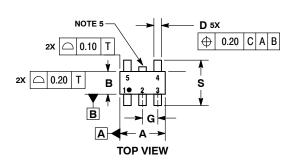
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

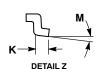


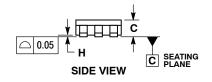


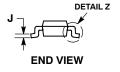
TSOP-5 **CASE 483 ISSUE N** 

**DATE 12 AUG 2020** 









#### NOTES:

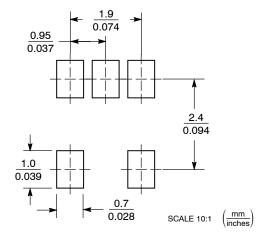
- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE
  MINIMUM THICKNESS OF BASE MATERIAL.
- MINIMUM I HICKNESS OF BASE MAI EHIAL.

  DIMENSIONS A AND B DO NOT INCLUDE MOLD
  FLASH, PROTRUSIONS, OR GATE BURRS. MOLD
  FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT
  EXCEED 0.15 PER SIDE. DIMENSION A.

  OPTIONAL CONSTRUCTION: AN ADDITIONAL
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS				
DIM	MIN MAX				
Α	2.85	3.15			
В	1.35	1.65			
С	0.90	1.10			
D	0.25	0.50			
G	0.95	BSC			
Н	0.01	0.10			
J	0.10	0.26			
K	0.20	0.60			
М	0 °	10 °			
S	2.50	3.00			

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***





XXX = Specific Device Code XXX = Specific Device Code

= Assembly Location = Date Code = Year = Pb-Free Package

= Work Week W = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

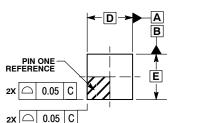
DOCUMENT NUMBER:	98ARB18753C	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSOP-5		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

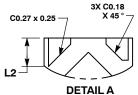


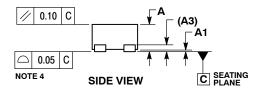
#### UDFN4 1.0x1.0, 0.65P CASE 517CU **ISSUE A**

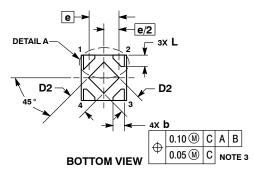
**DATE 18 DEC 2014** 



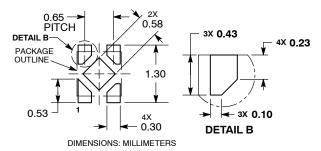
**TOP VIEW** 







#### **RECOMMENDED MOUNTING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSION 6 APPLIES TO PLATED TERMINAL
- AND IS MEASURED BETWEEN 0.03 AND 0.07 FROM THE TERMINAL TIPS.
  COPLANARITY APPLIES TO THE EXPOSED
- PAD AS WELL AS THE TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α		0.60	
A1	0.00	0.05	
А3	0.15 REF		
b	0.20	0.30	
D	1.00 BSC		
D2	0.38	0.58	
Е	1.00 BSC		
Φ	0.65 BSC		
L	0.20	0.30	
L2	0.27	0.37	

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

= Date Code Μ

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON76666F	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	UDFN4, 1.0X1.0, 0.65P		PAGE 1 OF 1

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales